

INFORMATION DISCLOSURE CITATION

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Applicants	Katsuyuki SEKINE et al.		
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U.S. PATENT DOCUMENTS							
Examiner Initial*		Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS							
		Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
WB	YASUDA, Y. et al., "Radical Nitridation in Multi-Oxide Process for 100nm Generation CMOS Technology", 2001 Symposium on VLSI Technology Digest of Technical Papers, 2 pages, (2001).
WB	CHEN, C. H. et al., "Downscaling Limit of Equivalent Oxide Thickness in Formation of Ultrathin Gate Dielectric by Thermal-Enhanced Remote Plasma Nitridation", IEEE Transactions on Electron Devices, Vol. 49, No. 5, pp. 840-846, (May 2002).

Examiner	<i>William M. Brewster</i>	Date Considered	1 FEB 06
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			
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